

SANYO Semiconductors

DATA SHEET

An ON Semiconductor Company



N-Channel Silicon MOSFET 2SK4196LS — General-Purpose Switching Device **Applications**

• Input capacitance Ciss=360pF

Features

- ON-resistance $R_{DS}(on)=1.2\Omega$ (typ.)
- 10V drive

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		500	V
Gate-to-Source Voltage	VGSS		±30	V
Drain Current (DC)	I _{Dc} *1	Limited only by maximum temperature Tch=150°C	5.5	А
	I _{Dpack} *2	Tc=25°C (SANYO's ideal heat dissipation condition)*3	5.0	А
Drain Current (Pulse)	IDP	PW≤10µs, duty cycle≤1%	21	А
Allowable Power Dissipation	De		2.0	W
	PD	Tc=25°C (SANYO's ideal heat dissipation condition)*3	30	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C
Avalanche Energy (Single Pulse) *4	EAS		83	mJ
Avalanche Current *5	IAV		5.5	А

Note :*1 Shows chip capability

*2 Package limited

*3 SANYO's condition is radiation from backside.

The method is applying silicone grease to the backside of the device and attaching the device to water-cooled radiator made of aluminium. *4 VDD=50V, L=5mH, IAV=5.5A (Fig.1)

2SK4196LS-1E

2.54

2.76

1 : Gate 2 : Drain 3 : Source

SANYO : TO-220F-3FS

*5 L≤5mH, single pulse

3.3

15.87

2.98

2 54

Θ

3.68

0.5

Package Dimensions

10.16

 \odot

Θ

unit : mm (typ)

Ø3.18

3.23

1.47 MA

7528-001

15.8

Product & Package Information

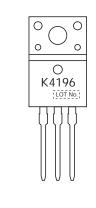
 Package : TO-220F-3FS : SC-67

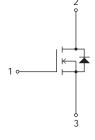
• JEITA, JEDEC

- Minimum Packing Quantity : 50 pcs./magazine

Marking

Electrical Connection





SANYO Semiconductor Co., Ltd. http://www.sanyosemi.com/en/network/

91212 TKIM TC-00002811/O2208OB MSIM TC-00001651 No. A1233-1/7

Electrical Characteristics at Ta=25°C

Parameter	Cirrente e l			Ratings			
Parameter	Symbol	Conditions	min	typ	max	Unit	
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=10mA, VGS=0V	500			V	
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =400V, V _{GS} =0V			100	μΑ	
Gate-to-Source Leakage Current	IGSS	V _{GS} =±30V, V _{DS} =0V			±100	nA	
Cutoff Voltage	VGS(off)	V _{DS} =10V, I _D =1mA	3		5	V	
Forward Transfer Admittance	yfs	VDS=10V, ID=2.8A	1.3	2.5		S	
Static Drain-to-Source On-State Resistance	R _{DS} (on)	ID=2.8A, VGS=10V		1.2	1.56	Ω	
Input Capacitance	Ciss			360		pF	
Output Capacitance	Coss	V _{DS} =30V, f=1MHz		77		pF	
Reverse Transfer Capacitance	Crss			17		рF	
Turn-ON Delay Time	t _d (on)			13		ns	
Rise Time	tr			32		ns	
Turn-OFF Delay Time	t _d (off)	See Fig.2		39		ns	
Fall Time	tf	1		18		ns	
Total Gate Charge	Qg			14.6		nC	
Gate-to-Source Charge	Qgs	V _{DS} =200V, V _{GS} =10V, I _D =5.5A		3.2		nC	
Gate-to-Drain "Miller" Charge	Qgd	1		8.8		nC	
Diode Forward Voltage	V _{SD}	IS=5.5A, VGS=0V		0.9	1.2	V	

Fig.1 Unclamped Inductive Switching Test Circuit

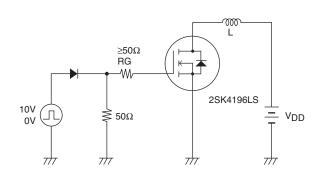
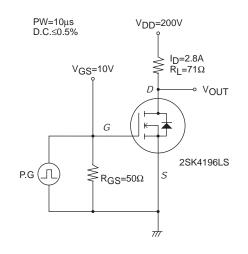
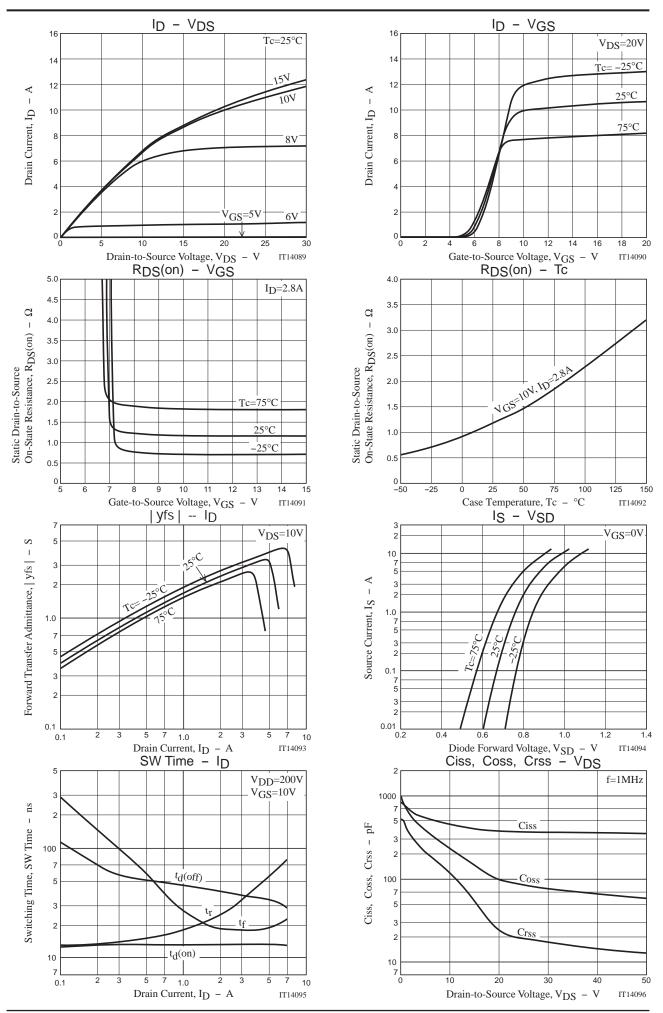


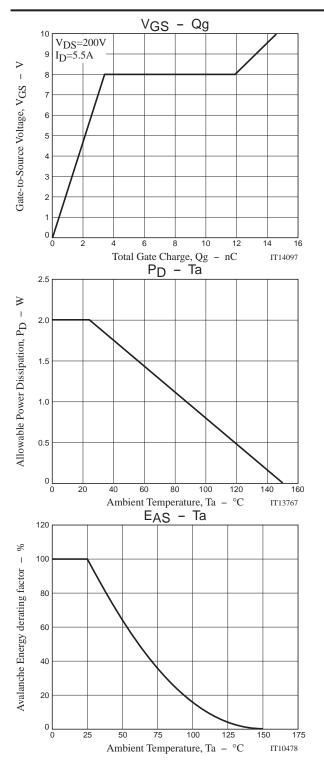
Fig.2 Switching Time Test Circuit

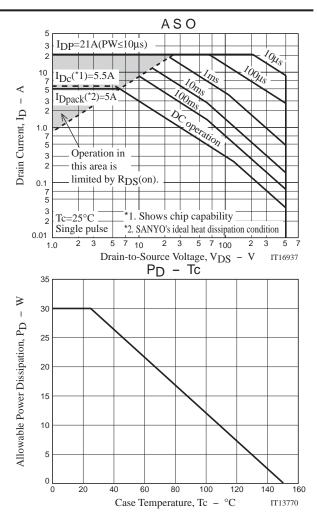


Ordering Information

Device Package		Shipping	memo	
2SK4196LS-1E TO-220F-3FS		50pcs./magazine	Pb Free	







Magazine Specification 2SK4196LS-1E

1. Packing Format

Package Name Magazine Name		Maximum Number of devices contained (pcs)			Packing format		
			Inner box	Quter dax	Inner BOX	Quter BOX	
TO-220F-3F\$	TO-220F	50	1,000	4,000	SPD-0V0001 20 magazines contained Dimensions:mm (external) 568×150×55	SPT-081029 4 inner boxes contained Dimensions:mm {external} 590×225×178	

2. Magazine dimensions (unit:mm)

3.5

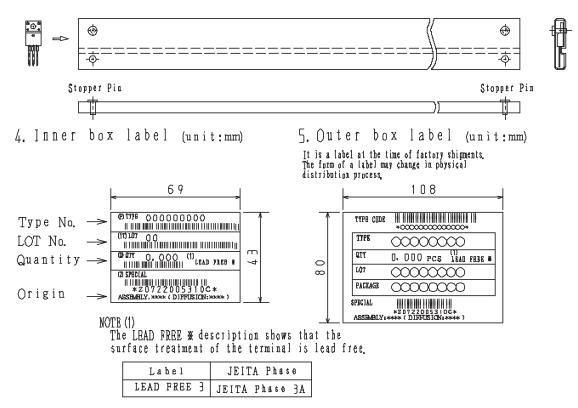
0.7



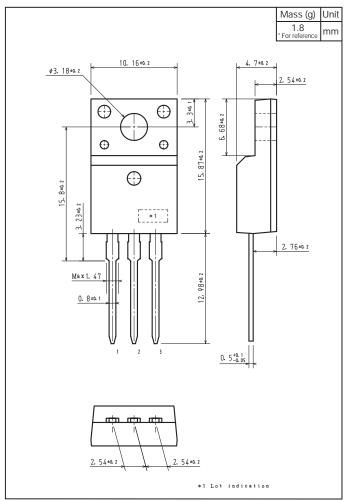
19

Tolerance=±(), 3mm Thickness=(), 7±(), 2mm Length =532, 5±2mm Material =PVC (Antistatic treatment)

3. Storage method to magazine



Outline Drawing 2SK4196LS-1E



Note on usage : Since the 2SK4196LS is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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